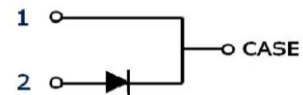
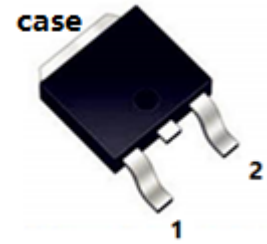


$V_{RRM} = 650\text{ V}$
 $I_F(T_C=155^\circ\text{C}) = 2.4\text{ A}$
 $Q_C = 9.8\text{ nC}$

Features:

- Extremely low reverse current
- No reverse recovery current
- Temperature independent switching
- Positive temperature coefficient on V_F
- Excellent surge current capability
- Low Capacitive charge



Benefits

- Essentially No switching losses
- System efficiency improvement over Si Diodes
- Increased power density
- Enabling higher switching frequency
- Reduction of Heat Sink Requirements
- System Cost savings due to smaller magnetics
- Reduced EMI



Applications

- Switch Mode Power Supplies (SMPS)
- Uninterruptable power supplies
- Motor Drivers
- Power Factor Correction

Pacakge Pin definitions

- Pin1- Cathode
- Pin2- Anode

Package Parameters

Part Number	Marking	Package
B1D02065E	B1D02065E	TO-252-2L

Maximum ratings

Symbol	Parameter	Test conditions	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		650	V
V_{RSM}	Surge Peak Reverse Voltage		650	V
I_F	Continuous Forward Current	$T_c=25^{\circ}\text{C}$ $T_c=135^{\circ}\text{C}$ $T_c=155^{\circ}\text{C}$	8 3.6 2.4	A
I_{FSM}	Non-Repetitive Forward Surge Current	$T_c=25^{\circ}\text{C}$, $t_p=10\text{ms}$, sine halfwave	19	A
$\int i^2 dt$	i^2t Value	$T_c=25^{\circ}\text{C}$, $t_p=10\text{ms}$	1.8	A^2S
P_{tot}	Power Dissipation	$T_c=25^{\circ}\text{C}$ $T_c=110^{\circ}\text{C}$	39 17	W
T_j	Operating junction temperature		-55~175	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~135	$^{\circ}\text{C}$

Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal resistance from junction to case		3.76		K/W
$R_{th(ja)}$	Thermal resistance from junction to ambient		96.7		K/W

Electrical Characteristics
Static Characteristics (T_j=25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V _{DC}	DC blocking voltage	T _j =25°C	650			V
V _F	Diode forward voltage	I _F =2A T _j =25°C I _F =2A T _j =175°C		1.39 1.59		V
I _R	Reverse current	V _R =650V T _j =25°C V _R =650V T _j =175°C		1 6		μA

Dynamic Characteristics (T_j=25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
Q _C	Total capacitive charge	V _R =400V T _j =25°C $Q_C = \int_0^{V_R} C(V)dV$		9.8		nC
C	Total Capacitance	V _R =1V f=1MHz V _R =300V f=1MHz V _R =600V f=1MHz		111 18.7 18.5		pF

Typical Performance

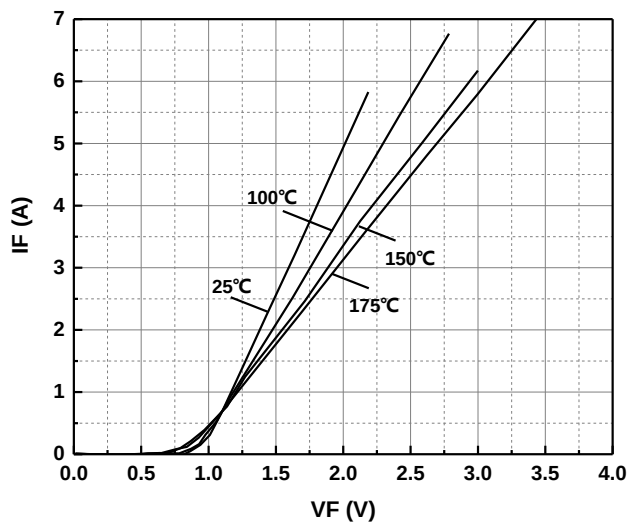


Figure 1. Typical forward characteristics

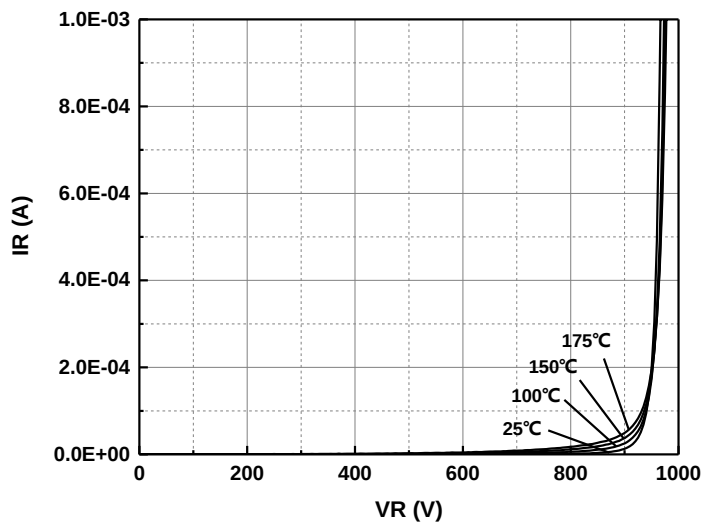


Figure 2. Typical reverse current as function of reverse voltage

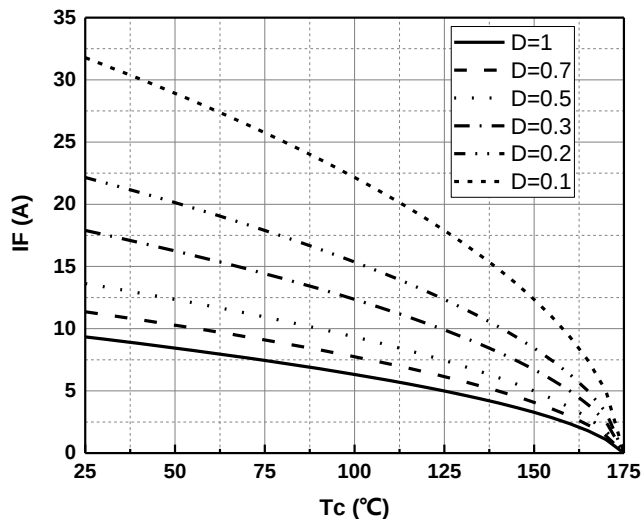


Figure 3. Diode forward current as function of temperature, D=duty cycle

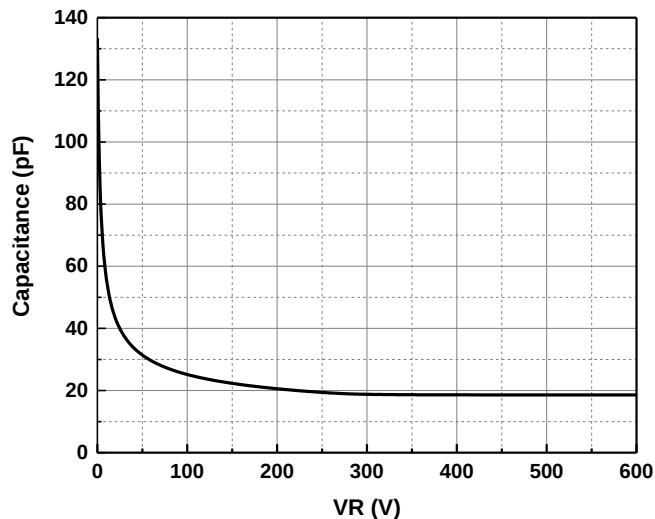


Figure 4. Typical capacitance as function of reverse voltage, $C=f(V_R)$; $T_J=25^\circ\text{C}$; $f=1\text{ MHz}$

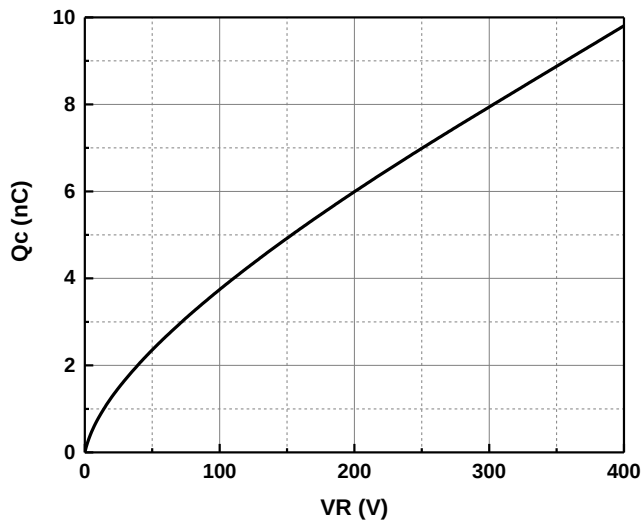


Figure 5. **Typical reverse charge as function of reverse voltage**

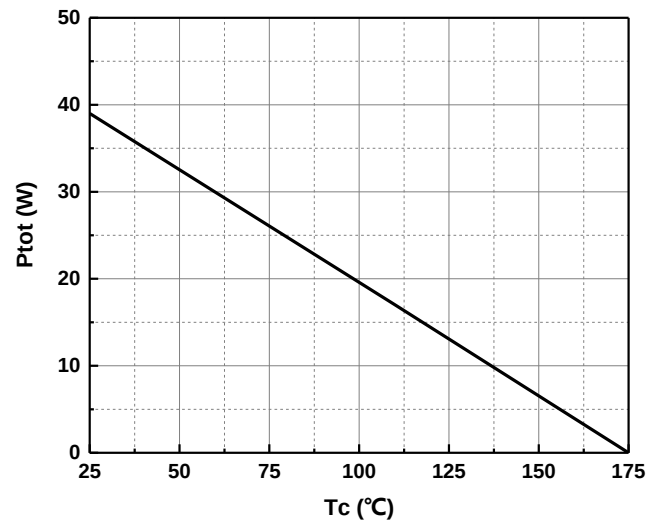


Figure 6. **Power dissipation as function of case temperature**

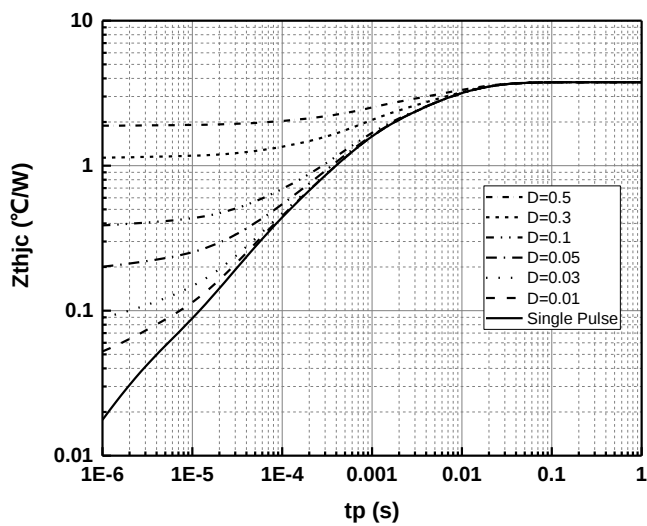
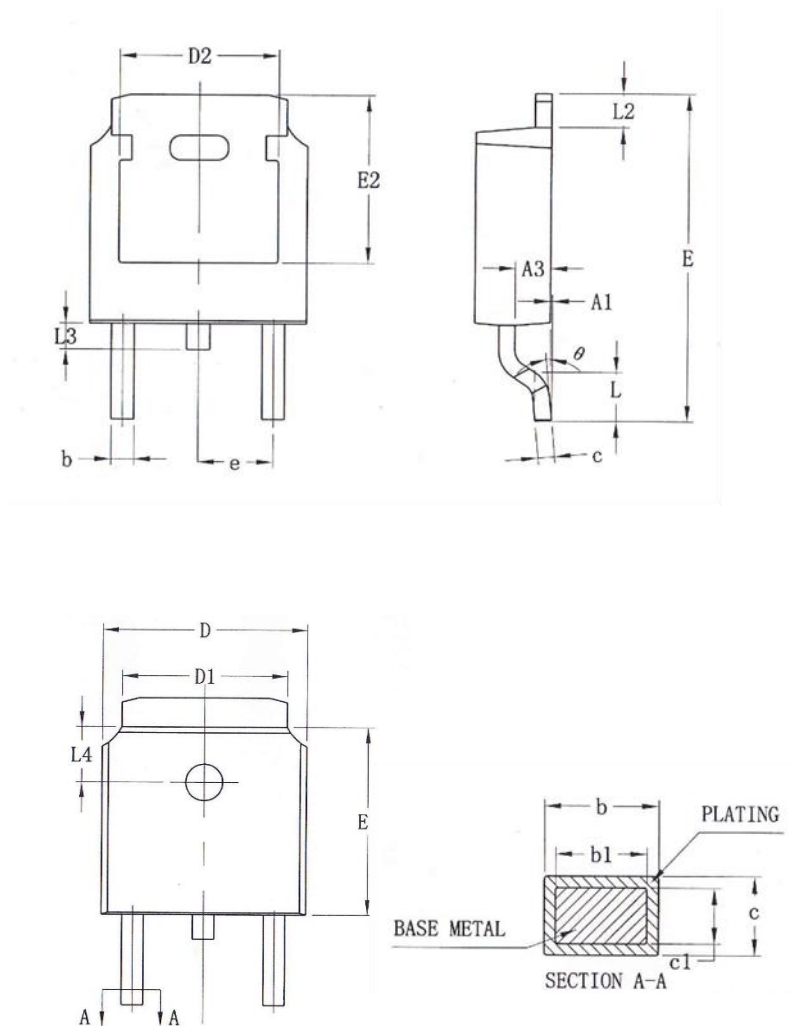


Figure 7. **Max. transient thermal impedance, $Z_{th,jc}=f(t)$, parameter: $D=t / T$**

Package Dimensions



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A1	0.00	—	0.10
A2	2.20	2.30	2.40
A3	1.02	1.07	1.12
b	0.74	—	0.82
b1	0.73	0.76	0.79
c	0.51	—	0.55
c1	0.50	0.51	0.52
D	6.50	6.60	6.70
D1	5.33REF		
D2	4.83REF		
E	9.90	10.10	10.30
E1	6.00	6.10	6.20
E2	5.30REF		
e	2.286BSC		
L	1.40	1.50	1.60
L2	0.90	—	1.25
L3	0.60	0.80	1.00
L4	1.70	1.80	1.90
θ	0		8°

Revision History**2019.12.07 Rev. 1.0****Previous Revision**

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